

Fabrizio Roccaforte

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332
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60
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350
ext. papers

6,603
ext. citations

2.4
avg, IF

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L-index

#	Paper	IF	Citations
332	Richardson's constant in inhomogeneous silicon carbide Schottky contacts. <i>Journal of Applied Physics</i> , 2003 , 93, 9137-9144	2.5	201
331	Emerging trends in wide band gap semiconductors (SiC and GaN) technology for power devices. <i>Microelectronic Engineering</i> , 2018 , 187-188, 66-77	2.5	163
330	Ohmic contacts to Gallium Nitride materials. <i>Applied Surface Science</i> , 2016 , 383, 324-345	6.7	153
329	Barrier inhomogeneity and electrical properties of Pt/GaN Schottky contacts. <i>Journal of Applied Physics</i> , 2007 , 102, 113701	2.5	143
328	Structural and electrical characterisation of titanium and nickel silicide contacts on silicon carbide. <i>Microelectronic Engineering</i> , 2002 , 60, 269-282	2.5	114
327	Recent advances on dielectrics technology for SiC and GaN power devices. <i>Applied Surface Science</i> , 2014 , 301, 9-18	6.7	97
326	Review of technology for normally-off HEMTs with p-GaN gate. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 96-106	4.3	95
325	An Overview of Normally-Off GaN-Based High Electron Mobility Transistors. <i>Materials</i> , 2019 , 12,	3.5	92
324	Electronic transport at monolayer-bilayer junctions in epitaxial graphene on SiC. <i>Physical Review B</i> , 2012 , 86,	3.3	79
323	Challenges for energy efficient wide band gap semiconductor power devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2063-2071	1.6	78
322	Surface and interface issues in wide band gap semiconductor electronics. <i>Applied Surface Science</i> , 2010 , 256, 5727-5735	6.7	75
321	Highly reproducible ideal SiC Schottky rectifiers: effects of surface preparation and thermal annealing on the Ni/6H-SiC barrier height. <i>Applied Physics A: Materials Science and Processing</i> , 2003 , 77, 827-833	2.6	73
320	Temperature dependence of the specific resistance in TiAl/NiAu contacts on n-type GaN. <i>Journal of Applied Physics</i> , 2006 , 100, 123706	2.5	67
319	Schottky-ohmic transition in nickel silicide/SiC-4H system: is it really a solved problem?. <i>Microelectronic Engineering</i> , 2003 , 70, 519-523	2.5	67
318	OHMIC CONTACTS TO SiC. <i>International Journal of High Speed Electronics and Systems</i> , 2005 , 15, 781-820.	0.5	65
317	High responsivity 4H-SiC Schottky UV photodiodes based on the pinch-off surface effect. <i>Applied Physics Letters</i> , 2006 , 89, 081111	3.4	63
316	Ambipolar MoS Transistors by Nanoscale Tailoring of Schottky Barrier Using Oxygen Plasma Functionalization. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 23164-23174	9.5	62

315	SiO ₂ /4H-SiC interface doping during post-deposition-annealing of the oxide in N ₂ O or POCl ₃ . <i>Applied Physics Letters</i> , 2013 , 103, 153508	3.4	61
314	Structural and electrical properties of Ni/Ti Schottky contacts on silicon carbide upon thermal annealing. <i>Journal of Applied Physics</i> , 2004 , 96, 4313-4318	2.5	60
313	Self-organization of gold nanoclusters on hexagonal SiC and SiO ₂ surfaces. <i>Journal of Applied Physics</i> , 2007 , 101, 064306	2.5	59
312	Nanoscale inhomogeneity of the Schottky barrier and resistivity in MoS ₂ multilayers. <i>Physical Review B</i> , 2015 , 92,	3.3	58
311	Improvement of high temperature stability of nickel contacts on n-type 6H-SiC. <i>Applied Surface Science</i> , 2001 , 184, 295-298	6.7	58
310	Current transport in graphene/AlGa _n /Ga _n vertical heterostructures probed at nanoscale. <i>Nanoscale</i> , 2014 , 6, 8671-80	7.7	57
309	Structural and transport properties in alloyed Ti/Al Ohmic contacts formed on p-type Al-implanted 4H-SiC annealed at high temperature. <i>Journal Physics D: Applied Physics</i> , 2011 , 44, 255302	3	57
308	Relaxation and crystallization of amorphous silicon carbide probed by optical measurements. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1997 , 76, 323-333		57
307	Vertical Transistors Based on 2D Materials: Status and Prospects. <i>Crystals</i> , 2018 , 8, 70	2.3	56
306	Nanoscale carrier transport in Ti/Al/Ni/Au Ohmic contacts on AlGa _n epilayers grown on Si(111). <i>Applied Physics Letters</i> , 2006 , 89, 022103	3.4	56
305	Temperature behavior of inhomogeneous Pt/GaN Schottky contacts. <i>Applied Physics Letters</i> , 2007 , 90, 092119	3.4	55
304	Highly Efficient Low Reverse Biased 4H-SiC Schottky Photodiodes for UV-Light Detection. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 1782-1784	2.2	53
303	Effects of annealing temperature on the degree of inhomogeneity of nickel-silicide/SiC Schottky barrier. <i>Journal of Applied Physics</i> , 2005 , 98, 023713	2.5	52
302	Nanoscale transport properties at silicon carbide interfaces. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 223001	3	51
301	Critical issues for interfaces to p-type SiC and GaN in power devices. <i>Applied Surface Science</i> , 2012 , 258, 8324-8333	6.7	47
300	Correlation between microstructure and temperature dependent electrical behavior of annealed Ti/Al/Ni/Au Ohmic contacts to AlGa _n /Ga _n heterostructures. <i>Applied Physics Letters</i> , 2013 , 103, 201604	3.4	47
299	Limiting mechanism of inversion channel mobility in Al-implanted lateral 4H-SiC metal-oxide semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2011 , 99, 072117	3.4	47
298	Acceptor, compensation, and mobility profiles in multiple Al implanted 4H-SiC. <i>Applied Physics Letters</i> , 2007 , 91, 202104	3.4	46

297	New Achievements on CVD Based Methods for SiC Epitaxial Growth. <i>Materials Science Forum</i> , 2005 , 483-485, 67-72	0.4	46
296	Microscopic mechanisms of graphene electrolytic delamination from metal substrates. <i>Applied Physics Letters</i> , 2014 , 104, 233105	3.4	45
295	Size-dependent Schottky Barrier Height in self-assembled gold nanoparticles. <i>Applied Physics Letters</i> , 2006 , 89, 243113	3.4	45
294	Characterization of SiO ₂ /4H-SiC Interfaces in 4H-SiC MOSFETs: A Review. <i>Energies</i> , 2019 , 12, 2310	3.1	44
293	Correlating macroscopic and nanoscale electrical modifications of SiO ₂ /4H-SiC interfaces upon post-oxidation-annealing in N ₂ O and POCl ₃ . <i>Applied Physics Letters</i> , 2012 , 101, 193501	3.4	44
292	Electro-structural evolution and Schottky barrier height in annealed Au/Ni contacts onto p-GaN. <i>Journal of Applied Physics</i> , 2011 , 110, 123703	2.5	43
291	Thermal stability of the current transport mechanisms in Ni-based Ohmic contacts on n- and p-implanted 4H-SiC. <i>Semiconductor Science and Technology</i> , 2014 , 29, 075018	1.8	42
290	Toward an ideal Schottky barrier on 3C-SiC. <i>Applied Physics Letters</i> , 2009 , 95, 081907	3.4	41
289	Transport localization in heterogeneous Schottky barriers of quantum-defined metal films. <i>Europhysics Letters</i> , 2006 , 74, 686-692	1.6	40
288	Effects of Annealing Treatments on the Properties of Al/Ti/p-GaN Interfaces for Normally OFF p-GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2735-2741	2.9	39
287	Fowler-Nordheim tunneling at SiO ₂ /4H-SiC interfaces in metal-oxide-semiconductor field effect transistors. <i>Applied Physics Letters</i> , 2014 , 105, 142108	3.4	39
286	Normal and abnormal grain growth in nanostructured gold film. <i>Journal of Applied Physics</i> , 2009 , 105, 054311	2.5	39
285	Atomic Force Microscopy Study of the Kinetic Roughening in Nanostructured Gold Films on SiO ₂ . <i>Nanoscale Research Letters</i> , 2009 , 4, 262-8	5	39
284	Solid phase epitaxial regrowth of ion beam-amorphized α -quartz. <i>Applied Physics Letters</i> , 1998 , 73, 1349-1351	3.4	39
283	Influence of high-temperature GaN annealed surface on the electrical properties of Ni/GaN Schottky contacts. <i>Journal of Applied Physics</i> , 2008 , 104, 093706	2.5	38
282	Ripple topography of ion-beam-eroded graphite: A key to ion-beam-induced damage tracks. <i>Europhysics Letters</i> , 2000 , 50, 209-215	1.6	38
281	Nanoscale current transport through Schottky contacts on wide bandgap semiconductors. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 789		37
280	Graphene p-Type Doping and Stability by Thermal Treatments in Molecular Oxygen Controlled Atmosphere. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 22718-22723	3.8	36

279	Epitaxial NiO gate dielectric on AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2012 , 100, 063511	3.4	35
278	Kinetic mechanism of the thermal-induced self-organization of Au/Si nanodroplets on Si(100): Size and roughness evolution. <i>Journal of Applied Physics</i> , 2008 , 104, 024310	2.5	34
277	Interface Electrical Properties of AlO Thin Films on Graphene Obtained by Atomic Layer Deposition with an in Situ Seedlike Layer. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 7761-7771	9.5	33
276	Graphene integration with nitride semiconductors for high power and high frequency electronics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600460	1.6	33
275	Crystallisation mechanism of amorphous silicon carbide. <i>Applied Surface Science</i> , 2001 , 184, 123-127	6.7	33
274	Self-organization of Au nanoclusters on the SiO ₂ surface induced by 200keV-Ar ⁺ irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 257, 810-814	1.2	31
273	Microstructure of Au nanoclusters formed in and on SiO ₂ . <i>Superlattices and Microstructures</i> , 2008 , 44, 588-598	2.8	31
272	Slow and fast traps in metal-oxide-semiconductor capacitors fabricated on recessed AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2015 , 106, 142903	3.4	30
271	Impact of contact resistance on the electrical properties of MoS transistors at practical operating temperatures. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 254-263	3	29
270	Poole-Frenkel emission in epitaxial nickel oxide on AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2012 , 101, 172901	3.4	29
269	Defects and electrical behavior in 1MeV Si ⁺ -ion-irradiated 4H-BiC Schottky diodes. <i>Journal of Applied Physics</i> , 2006 , 99, 013515	2.5	29
268	Comparative study of gate oxide in 4H-SiC lateral MOSFETs subjected to post-deposition-annealing in N ₂ O and POCl ₃ . <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 115, 333-339	2.6	28
267	Effects of CD2 locus control region sequences on gene expression by retroviral and lentiviral vectors. <i>Blood</i> , 2001 , 98, 3607-17	2.2	28
266	Negative charge trapping effects in Al ₂ O ₃ films grown by atomic layer deposition onto thermally oxidized 4H-SiC. <i>AIP Advances</i> , 2016 , 6, 075021	1.5	28
265	Channel Mobility in GaN Hybrid MOS-HEMT Using SiO ₂ as Gate Insulator. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2893-2899	2.9	27
264	Influence of the surface morphology on the channel mobility of lateral implanted 4H-SiC(0001) metal-oxide-semiconductor field-effect transistors. <i>Journal of Applied Physics</i> , 2012 , 112, 084501	2.5	26
263	Micro- and nanoscale electrical characterization of large-area graphene transferred to functional substrates. <i>Beilstein Journal of Nanotechnology</i> , 2013 , 4, 234-42	3	26
262	Near interface traps in SiO ₂ /4H-SiC metal-oxide-semiconductor field effect transistors monitored by temperature dependent gate current transient measurements. <i>Applied Physics Letters</i> , 2016 , 109, 012102	3.4	26

261	Metal Organic Chemical Vapor Deposition of nickel oxide thin films for wide band gap device technology. <i>Thin Solid Films</i> , 2014 , 563, 50-55	2.2	25
260	Nanoscale structural and electrical evolution of Ta- and Ti-based contacts on AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 2013 , 114, 083717	2.5	25
259	Ti/Al ohmic contacts on AlGaIn/GaN heterostructures with different defect density. <i>Applied Surface Science</i> , 2014 , 314, 546-551	6.7	24
258	Ti/Al/W Ohmic contacts to p-type implanted 4H-SiC. <i>Journal of Applied Physics</i> , 2015 , 118, 035705	2.5	24
257	Ion irradiation of inhomogeneous Schottky barriers on silicon carbide. <i>Journal of Applied Physics</i> , 2005 , 97, 123502	2.5	24
256	Oxygen-activated epitaxial recrystallization of Li-implanted BiO ₂ . <i>Physical Review B</i> , 2000 , 61, 3327-3332	3.3	24
255	Effect of temperature bias annealing on the hysteresis and subthreshold behavior of multilayer MoS ₂ transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016 , 10, 797-801	2.5	23
254	High-Performance Graphene/AlGaIn/GaN Schottky Junctions for Hot Electron Transistors. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 2342-2354	4	23
253	From Schottky to Ohmic graphene contacts to AlGaIn/GaN heterostructures: Role of the AlGaIn layer microstructure. <i>Applied Physics Letters</i> , 2014 , 105, 063117	3.4	23
252	Crystallization process of amorphous silicon-carbon alloys. <i>Thin Solid Films</i> , 2002 , 411, 298-302	2.2	23
251	Genesis and evolution of extended defects: The role of evolving interface instabilities in cubic SiC. <i>Applied Physics Reviews</i> , 2020 , 7, 021402	17.3	22
250	Electrical behavior of AlGaIn/GaN heterostructures upon high-temperature selective oxidation. <i>Journal of Applied Physics</i> , 2009 , 106, 023703	2.5	22
249	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. <i>Carbon</i> , 2017 , 116, 722-732	10.4	21
248	Effect of air on oxygen p-doped graphene on SiO ₂ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2341-2344	1.6	21
247	Conduction Mechanisms at Interface of AlN/SiN Dielectric Stacks with AlGaIn/GaN Heterostructures for Normally-off High Electron Mobility Transistors: Correlating Device Behavior with Nanoscale Interfaces Properties. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 35383-35390	9.5	21
246	Electro-optical response of ion-irradiated 4H-SiC Schottky ultraviolet photodetectors. <i>Applied Physics Letters</i> , 2008 , 92, 093505	3.4	21
245	Tailoring the Ti/4H-SiC Schottky barrier by ion irradiation. <i>Applied Physics Letters</i> , 2004 , 85, 6152-6154	3.4	21
244	Silicon carbide pinch rectifiers using a dual-metal Ti-Ni/sub 2/Si Schottky barrier. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 1741-1747	2.9	21

243	Temperature dependence of the c-axis mobility in 6H-SiC Schottky diodes. <i>Applied Physics Letters</i> , 2003 , 83, 4181-4183	3.4	21
242	Electrical and structural properties of surfaces and interfaces in Ti/Al/Ni Ohmic contacts to p-type implanted 4H-SiC. <i>Applied Surface Science</i> , 2017 , 420, 331-335	6.7	20
241	Effect of high temperature annealing ($T > 1650$ °C) on the morphological and electrical properties of p-type implanted 4H-SiC layers. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 274-279	4.3	20
240	Epitaxial crystallization of amorphous SiO ₂ films deposited on single-crystalline α -quartz. <i>Applied Physics Letters</i> , 1999 , 75, 2903-2905	3.4	20
239	Nanoscale electrical and structural modification induced by rapid thermal oxidation of AlGaIn/GaN heterostructures. <i>Nanotechnology</i> , 2014 , 25, 025201	3.4	19
238	Photocurrent gain in 4H-SiC interdigit Schottky UV detectors with a thermally grown oxide layer. <i>Applied Physics Letters</i> , 2007 , 90, 223507	3.4	19
237	Epitaxial crystallization of keV-ion-bombarded α -quartz. <i>Journal of Applied Physics</i> , 2001 , 89, 3611-3618	2.5	19
236	Ion beam erosion of graphite surfaces studied by STM: Ripples, self-affine roughening and near-surface damage accumulation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 161-163, 958-962	1.2	19
235	High permittivity cerium oxide thin films on AlGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , 2013 , 103, 112905	3.4	18
234	Interdigit 4H-SiC Vertical Schottky Diode for Betavoltaic Applications. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 593-599	2.9	18
233	Interaction between dislocations and He-implantation-induced voids in GaN epitaxial layers. <i>Applied Physics Letters</i> , 2005 , 86, 211911	3.4	18
232	Angular distortion of Si clusters in α -SiC. <i>Europhysics Letters</i> , 2001 , 55, 674-678	1.6	18
231	Oxygen migration during epitaxial regrowth in Cs ⁺ -irradiated α -quartz investigated by means of nuclear reaction analysis. <i>Applied Physics Letters</i> , 2000 , 76, 3709-3711	3.4	18
230	Barrier inhomogeneity in vertical Schottky diodes on free standing gallium nitride. <i>Materials Science in Semiconductor Processing</i> , 2019 , 94, 164-170	4.3	17
229	Conductive Atomic Force Microscopy of Semiconducting Transition Metal Dichalcogenides and Heterostructures. <i>Nanomaterials</i> , 2020 , 10,	5.4	17
228	Temperature-dependent Fowler-Nordheim electron barrier height in SiO ₂ /4H-SiC MOS capacitors. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 38-42	4.3	17
227	Drift mobility in 4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , 2005 , 87, 142105	3.4	17
226	Effects of interface states and near interface traps on the threshold voltage stability of GaN and SiC transistors employing SiO ₂ as gate dielectric. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 01A101	1.3	16

225	Morphological and electrical properties of Nickel based Ohmic contacts formed by laser annealing process on n-type 4H-SiC. <i>Materials Science in Semiconductor Processing</i> , 2019 , 97, 62-66	4.3	16
224	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. <i>Advanced Electronic Materials</i> , 2020 , 6, 1901171	6.4	16
223	Advances in the fabrication of graphene transistors on flexible substrates. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 467-474	3	16
222	A look underneath the SiO ₂ /4H-SiC interface after N ₂ O thermal treatments. <i>Beilstein Journal of Nanotechnology</i> , 2013 , 4, 249-54	3	16
221	Improved Ni/3C-SiC contacts by effective contact area and conductivity increases at the nanoscale. <i>Applied Physics Letters</i> , 2009 , 94, 112104	3.4	16
220	Schottky-Ohmic Transition in Nickel Silicide/SiC System: Is it Really a Solved Problem?. <i>Materials Science Forum</i> , 2003 , 433-436, 721-724	0.4	16
219	Temperature dependent forward current-voltage characteristics of Ni/Au Schottky contacts on AlGa _N /Ga _N heterostructures described by a two diodes model. <i>Journal of Applied Physics</i> , 2017 , 121, 045701	2.5	15
218	Seed-Layer-Free Atomic Layer Deposition of Highly Uniform Al ₂ O ₃ Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1900097	4.6	15
217	. <i>IEEE Photonics Journal</i> , 2015 , 7, 1-6	1.8	15
216	Temperature and Light Induced Effects on the Capacitance of 4H-SiC Schottky Photodiodes. <i>IEEE Sensors Journal</i> , 2012 , 12, 1127-1130	4	15
215	Quantitative determination of depth carrier profiles in ion-implanted Gallium Nitride. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 257, 336-339	1.2	15
214	Nanoscale voltage tunable tunnel rectifier by gold nanostructures embedded in SiO ₂ . <i>Applied Physics Letters</i> , 2006 , 89, 263108	3.4	15
213	High growth rate process in a SiC horizontal CVD reactor using HCl. <i>Microelectronic Engineering</i> , 2006 , 83, 48-50	2.5	15
212	Direct Probing of Grain Boundary Resistance in Chemical Vapor Deposition-Grown Monolayer MoS ₂ by Conductive Atomic Force Microscopy. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900393	2.5	15
211	Comparison between thermal and plasma enhanced atomic layer deposition processes for the growth of HfO ₂ dielectric layers. <i>Journal of Crystal Growth</i> , 2020 , 539, 125624	1.6	15
210	Near-surface processing on AlGa _N /Ga _N heterostructures: a nanoscale electrical and structural characterization. <i>Nanoscale Research Letters</i> , 2011 , 6, 132	5	14
209	Thermodynamic Properties of Supported and Embedded Metallic Nanocrystals: Gold on/in SiO ₂ . <i>Nanoscale Research Letters</i> , 2008 , 3, 454-60	5	14
208	Network modification and epitaxial recrystallisation of ion-implanted Quartz. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1999 , 148, 692-697	1.2	14

207	Fabrication and Characterization of Graphene Heterostructures with Nitride Semiconductors for High Frequency Vertical Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700653	1.6	14
206	Two-dimensional electron gas insulation by local surface thin thermal oxidation in AlGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , 2008 , 92, 252101	3.4	13
205	Epitaxial Layers Grown with HCl Addition: A Comparison with the Standard Process. <i>Materials Science Forum</i> , 2006 , 527-529, 163-166	0.4	13
204	Substrate and atmosphere influence on oxygen p-doped graphene. <i>Carbon</i> , 2016 , 107, 696-704	10.4	13
203	Recent Advances in Seeded and Seed-Layer-Free Atomic Layer Deposition of High-K Dielectrics on Graphene for Electronics. <i>Journal of Carbon Research</i> , 2019 , 5, 53	3.3	12
202	Ti/Al-based contacts to p-type SiC and GaN for power device applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600357	1.6	12
201	Barrier Inhomogeneity of Ni Schottky Contacts to Bulk GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700613	1.6	11
200	Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 706-709	0.4	11
199	High efficiency 4H-SiC Schottky UV-photodiodes using self-aligned semitransparent contacts. <i>Superlattices and Microstructures</i> , 2007 , 41, 29-35	2.8	11
198	Microstructure and current transport in Ti/Al/Ni/Au ohmic contacts to n-type AlGaIn epilayers grown on Si(111). <i>Superlattices and Microstructures</i> , 2006 , 40, 373-379	2.8	11
197	Aluminum oxide nucleation in the early stages of atomic layer deposition on epitaxial graphene. <i>Carbon</i> , 2020 , 169, 172-181	10.4	11
196	Modification of the sheet resistance under Ti/Al/Ni/Au Ohmic contacts on AlGaIn/GaN heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 111-117	4.3	11
195	An insight into the epitaxial nanostructures of NiO and CeO ₂ thin film dielectrics for AlGaIn/GaN heterostructures. <i>Materials Chemistry and Physics</i> , 2015 , 162, 461-468	4.4	10
194	Electron trapping at SiO ₂ /4H-SiC interface probed by transient capacitance measurements and atomic resolution chemical analysis. <i>Nanotechnology</i> , 2018 , 29, 395702	3.4	10
193	3C-SiC Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiC Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). <i>Materials Science Forum</i> , 2018 , 924, 913-918	0.4	10
192	Impact of the Morphological and Electrical Properties of SiO ₂ /4H-SiC Interfaces on the Behavior of 4H-SiC MOSFETs. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, N3006-N3011	2	10
191	In-situ monitoring by Raman spectroscopy of the thermal doping of graphene and MoS ₂ in O ₂ -controlled atmosphere. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 418-424	3	10
190	Ni/4H-SiC interaction and silicide formation under excimer laser annealing for ohmic contact. <i>Materialia</i> , 2020 , 9, 100528	3.2	10

189	Current injection from metal to MoS ₂ probed at nanoscale by conductive atomic force microscopy. <i>Materials Science in Semiconductor Processing</i> , 2016 , 42, 174-178	4.3	9
188	Determining oxide trapped charges in Al ₂ O ₃ insulating films on recessed AlGa _N /Ga _N heterostructures by gate capacitance transients measurements. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 050307	1.4	9
187	Nanoscale probing of the lateral homogeneity of donors concentration in nitridated SiO ₂ /4H-SiC interfaces. <i>Nanotechnology</i> , 2016 , 27, 315701	3.4	9
186	Laminated Al ₂ O ₃ /HfO ₂ layers grown by atomic layer deposition for microelectronics applications. <i>Thin Solid Films</i> , 2016 , 601, 68-72	2.2	9
185	High resolution study of structural and electronic properties of epitaxial graphene grown on off-axis 4H-SiC (0001). <i>Journal of Crystal Growth</i> , 2014 , 393, 150-155	1.6	9
184	Electronic properties of epitaxial graphene residing on SiC facets probed by conductive atomic force microscopy. <i>Applied Surface Science</i> , 2014 , 291, 53-57	6.7	9
183	Nanoscale electro-structural characterisation of ohmic contacts formed on p-type implanted 4H-SiC. <i>Nanoscale Research Letters</i> , 2011 , 6, 158	5	9
182	On the Aging Effects of 4H-SiC Schottky Photodiodes Under High Intensity Mercury Lamp Irradiation. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 775-777	2.2	9
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70	Integration of 2D Materials with Nitrides for Novel Electronic and Optoelectronic Applications 2020 , 397-438		2
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68	Fabrication and Characterization of Ohmic Contacts to 3C-SiC Layers Grown on Silicon. <i>Materials Science Forum</i> , 2019 , 963, 485-489	0.4	2
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